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Si4542DY

30V Complementary PowerTrench® MOSFET

General Description

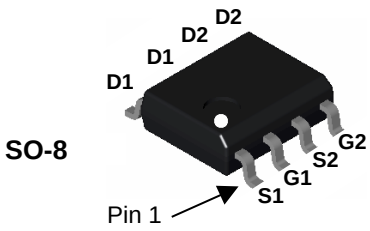
This complementary MOSFET device is produced using ON Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

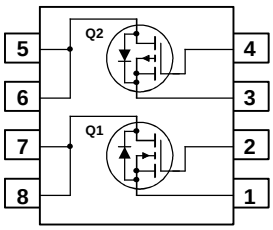
Applications

- DC/DC converter
- Power management

Features

- **Q1**: **N-Channel**
  6 A, 30 V $R_{DS(on)}$ = 28 mΩ @ V_{GS} = 10V
  $R_{DS(on)}$ = 35 mΩ @ V_{GS} = 4.5V
- **Q2**: **P-Channel**
  –6 A, –30 V $R_{DS(on)}$ = 32 mΩ @ V_{GS} = –10V
  $R_{DS(on)}$ = 45 mΩ @ V_{GS} = –4.5V





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Q1	Q2	Units
V_{DSS}	Drain-Source Voltage		30	–30	V
V_{GSS}	Gate-Source Voltage		±20	±20	V
I_D	Drain Current - Continuous	(Note 1a)	6	–6	A
	- Pulsed		20	–20	
P_D	Power Dissipation for Dual Operation		2		W
	Power Dissipation for Single Operation	(Note 1a)	1.6		
		(Note 1b)	1.2		
		(Note 1c)	1		
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +175		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
4542	Si4542DY	13"	12mm	2500 units

October-2017, Rev 1

Publication Order Number:
Si4542DY/D

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA V_{GS} = 0 V, I_D = –250 µA	Q1 Q2	30 –30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C I_D = –250 µA, Referenced to 25°C	Q1 Q2		23 –21		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V V_{DS} = –24 V, V_{GS} = 0 V	Q1 Q2			1 –1	µA
I_{GSS}	Gate-Body Leakage	V_{GS} = ±20 V, V_{DS} = 0 V V_{GS} = ±20 V, V_{DS} = 0 V	Q1 Q2			±100 ±100	nA
On Characteristics (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA V_{DS} = V_{GS}, I_D = –250 µA	Q1 Q2	1 –1	1.5 –1.7	3 –3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C I_D = –250 µA, Referenced to 25°C	Q1 Q2		–4 4		mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 6 A V_{GS} = 10 V, I_D = 6 A, T_J = 125°C V_{GS} = 4.5 V, I_D = 5 A	Q1		19 32 25	28 48 35	mΩ
		V_{GS} = –10 V, I_D = –6 A V_{GS} = –10 V, I_D = –6 A, T_J = 125°C V_{GS} = –4.5 V, I_D = –5 A	Q2		21 29 30	32 51 45	
$I_{D(on)}$	On-State Drain Current	V_{GS} = 10 V, V_{DS} = 5 V V_{GS} = –10 V, V_{DS} = –5 V	Q1 Q2	20 –20			A
g_{FS}	Forward Transconductance	V_{DS} = 15 V, I_D = 6 A V_{DS} = –10 V, I_D = –6 A	Q1 Q2		18 16		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	Q1 V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz Q2 V_{DS} = –15 V, V_{GS} = 0 V, f = 1.0 MHz	Q1 Q2		830 1540		pF
C_{oss}	Output Capacitance		Q1 Q2		185 400		pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		80 170		pF

Electrical Characteristics (continued)

T_A = 25°C unless otherwise noted

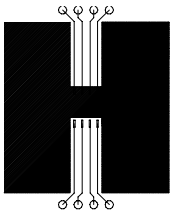
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Switching Characteristics (Note 2)							
$t_{d(on)}$	Turn-On Delay Time	Q1 V_{DS} = 15 V, I_D = 1 A, V_{GS} = 10V, R_{GEN} = 6 Ω Q2 V_{DS} = –15 V, I_D = –1 A, V_{GS} = –10 V, R_{GEN} = 6 Ω	Q1 Q2		6 13	12 24	ns
t_r	Turn-On Rise Time		Q1 Q2		10 22	18 35	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		18 47	29 75	ns
t_f	Turn-Off Fall Time		Q1 Q2		5 18	12 30	ns
Q_g	Total Gate Charge	Q1 V_{DS} = 15 V, I_D = 7.5 A, V_{GS} = 5 V Q2 V_{DS} = –10 V, I_D = –6 A, V_{GS} = –5V	Q1 Q2		9 15	13 20	nC
Q_{gs}	Gate-Source Charge		Q1 Q2		2.8 4		nC
Q_{gd}	Gate-Drain Charge		Q1 Q2		3.1 5		nC

Drain-Source Diode Characteristics and Maximum Ratings

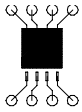
I_S	Maximum Continuous Drain-Source Diode Forward Current		Q1 Q2			1.3 –1.3	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.3 A (Note 2) V_{GS} = 0 V, I_S = –1.3 A (Note 2)	Q1 Q2		0.7 –0.7	1.2 –1.2	V

Notes:

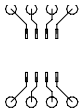
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in^2 pad of 2 oz copper



b) 125°C/W when mounted on a .02 in^2 pad of 2 oz copper



c) 135°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

PUBLICATION ORDERING INFORMATION

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